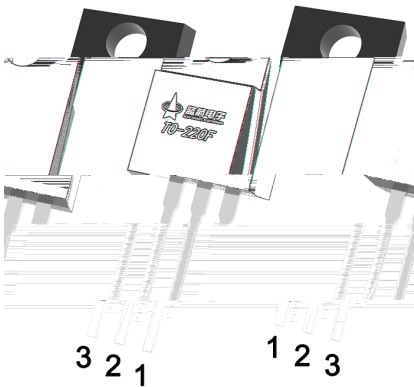
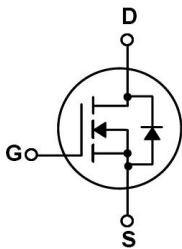


SiC

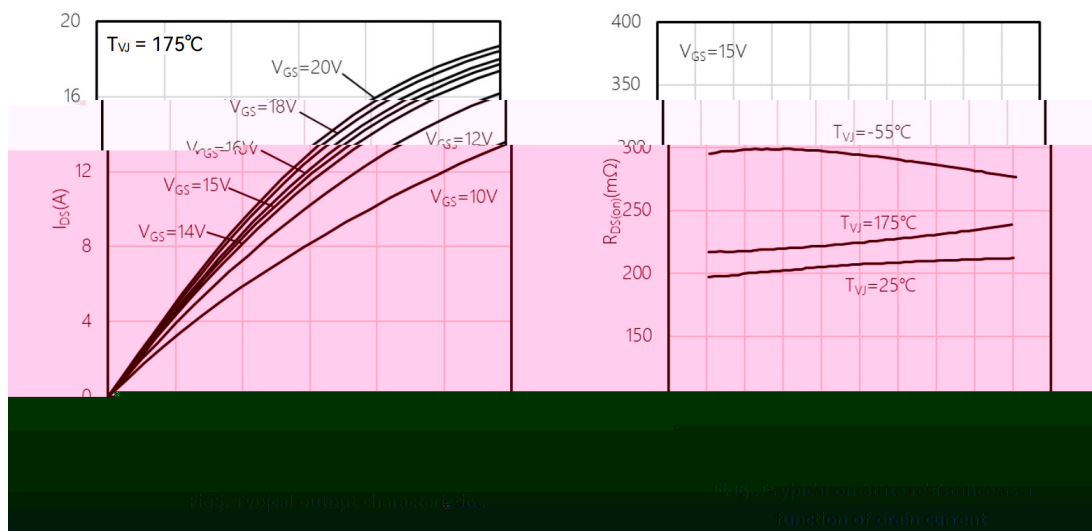
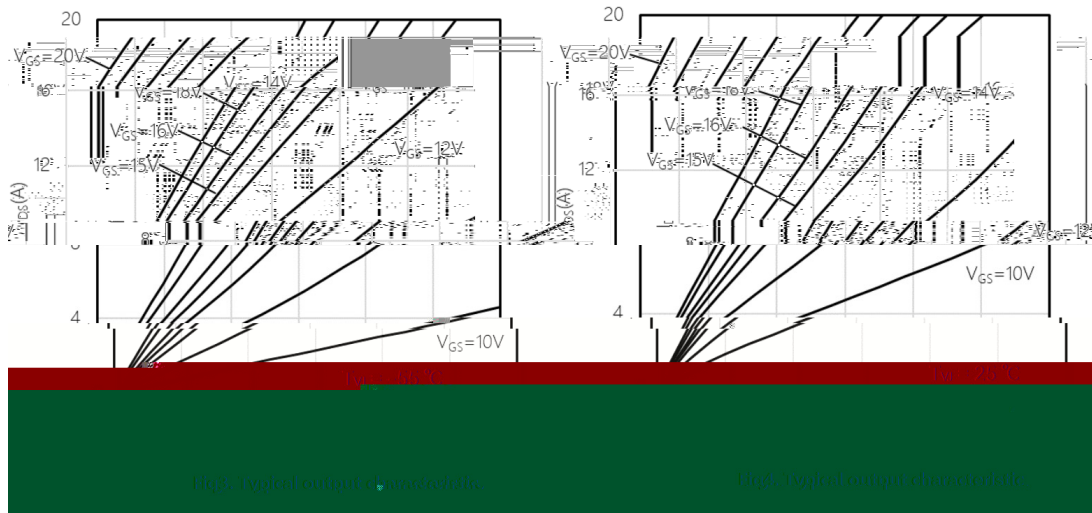
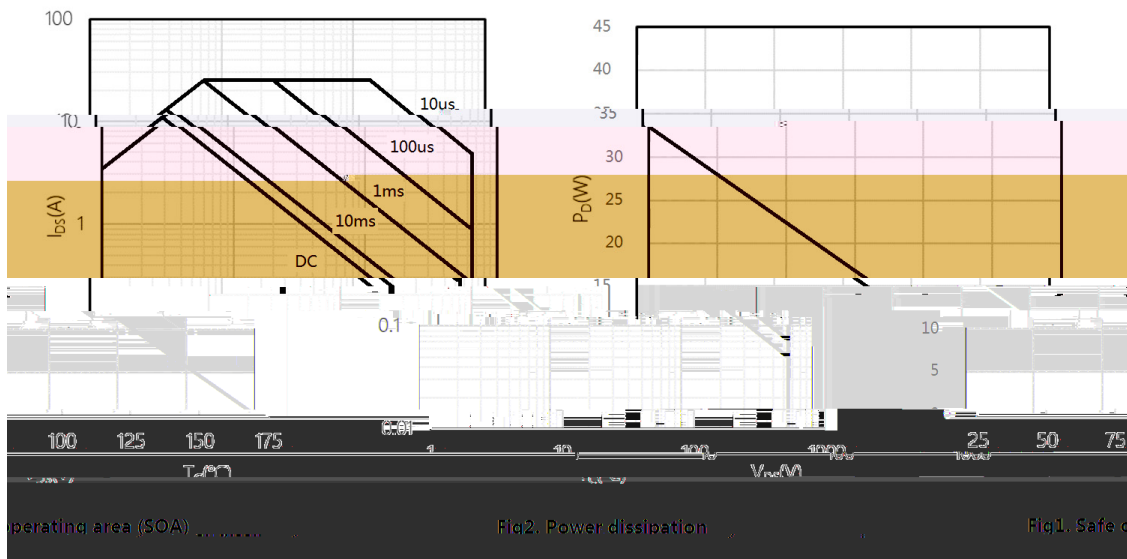
≤	Ω	Ω
≤	Ω	Ω

LED	PD	PC
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		μ Ω				
-						μ
-						
						Ω



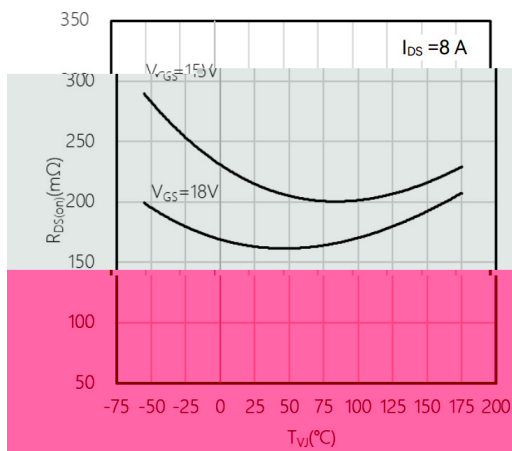


Fig5. Typical on-state resistance as a function of temperature

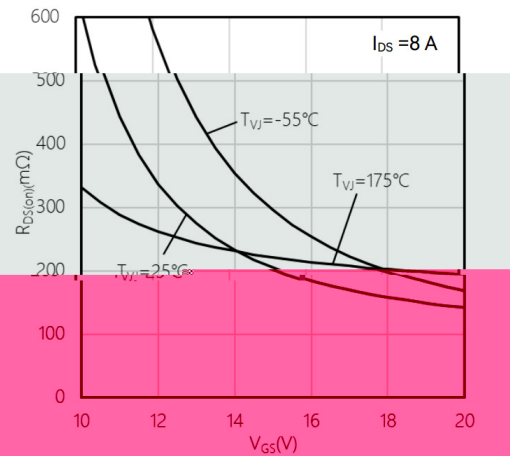


Fig6. Typical on-state resistance as a function of V_{GS}

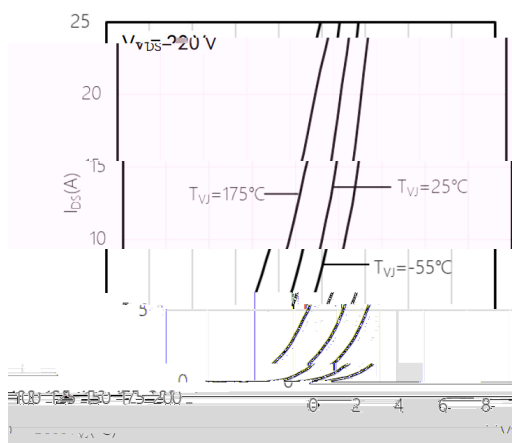


Fig9. Typical transfer characteristic of junction temperature

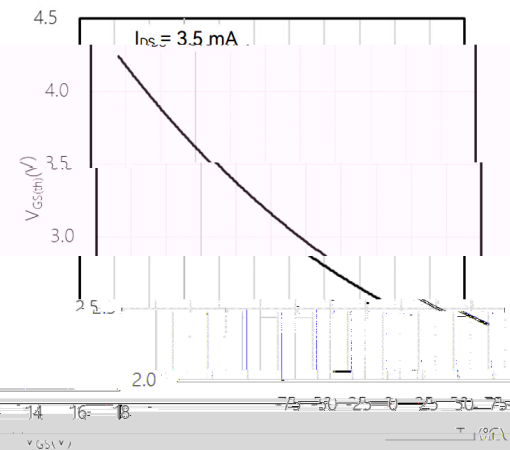


Fig10. Typical gate-source threshold voltage as a function of I_{DS}

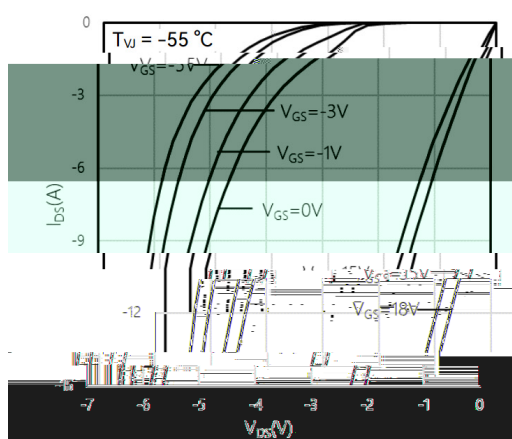


Fig11. Typical reverse drain current as a function of reverse drain voltage

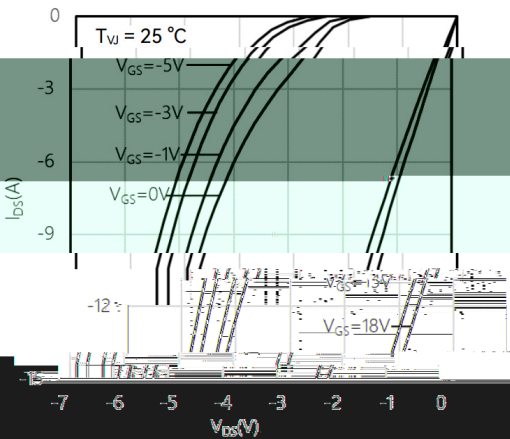
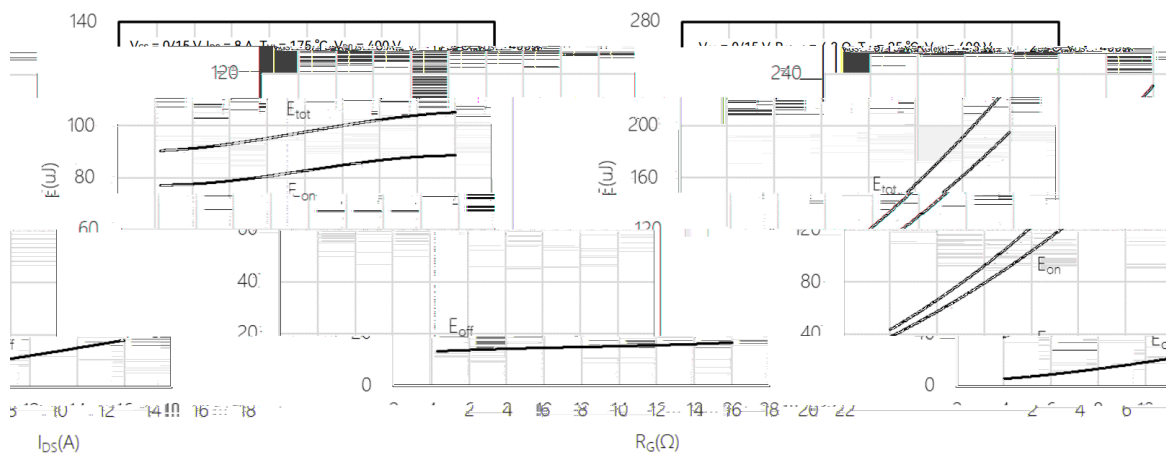
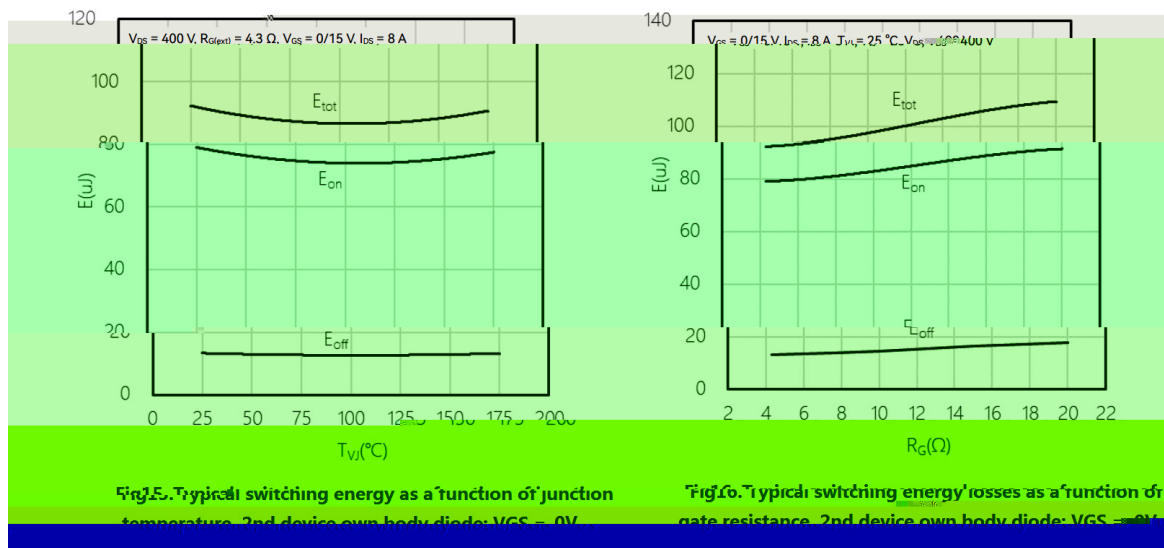
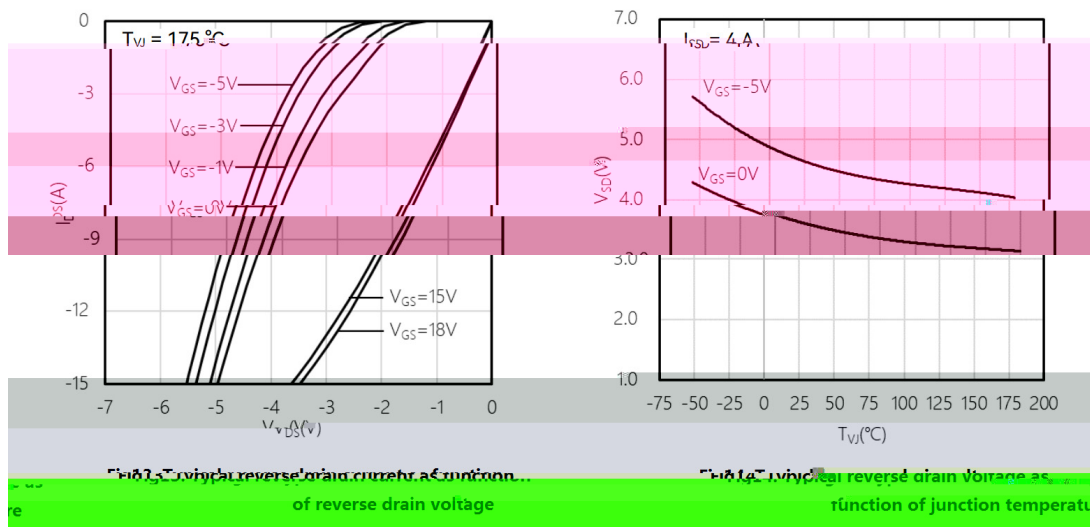


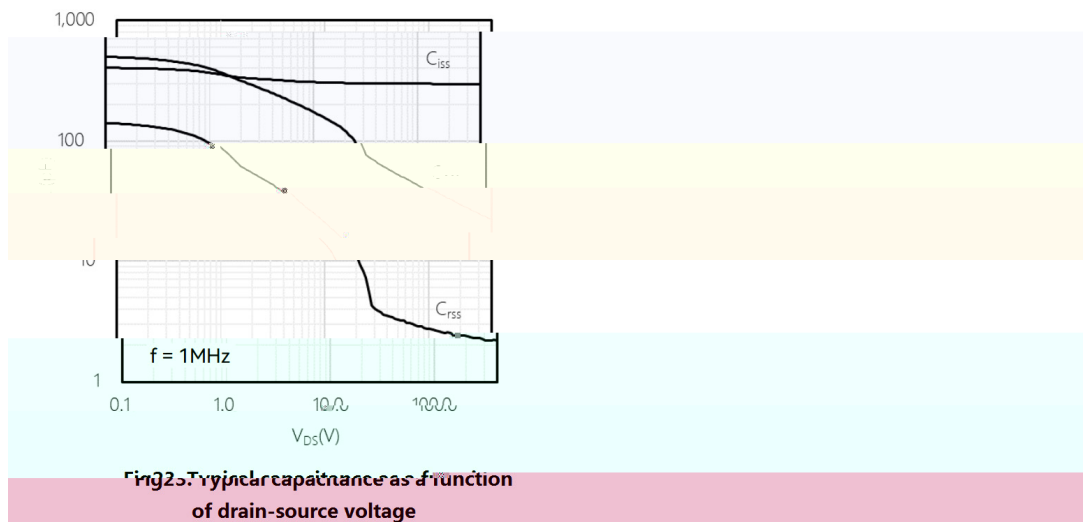
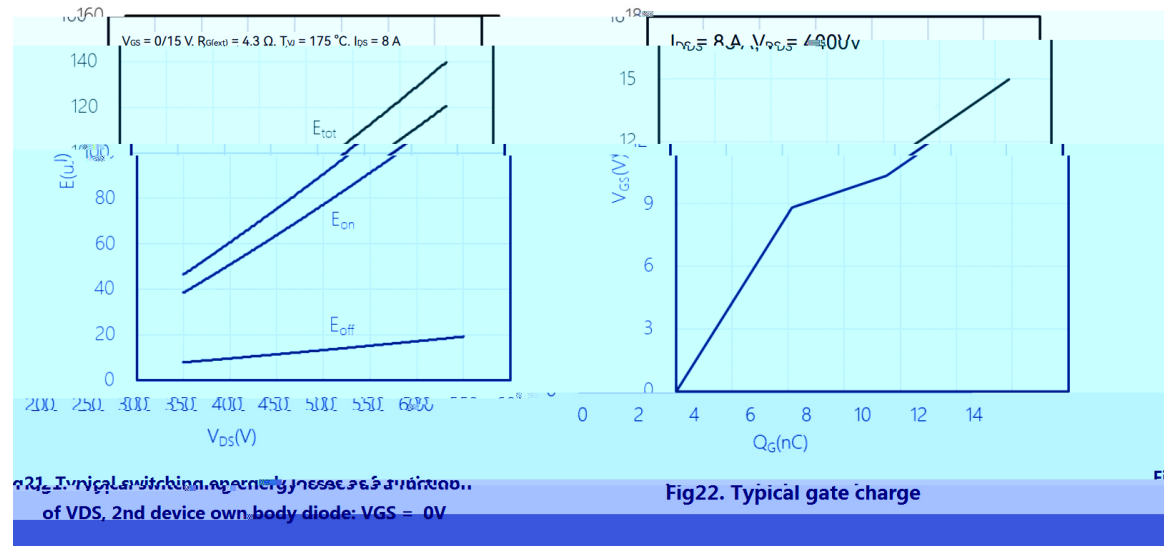
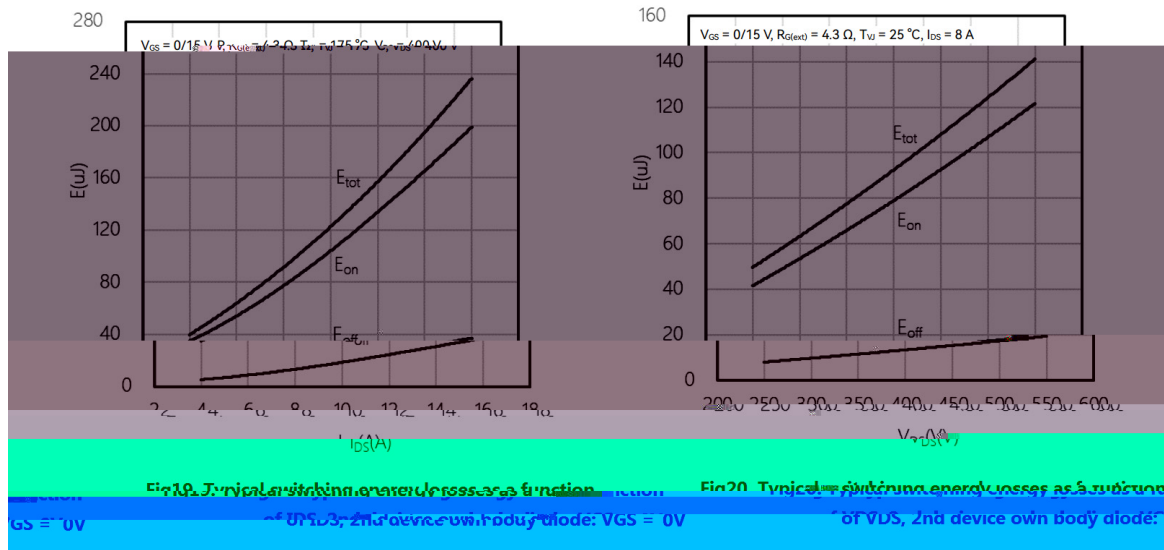
Fig12. Typical reverse drain current as a function of reverse drain voltage



Typical switching energy losses as a function of gate resistance, 2nd device own body diode: $V_{GS} = 0\text{V}$

Typical switching energy losses as a function of gate resistance, 2nd device own body diode: $V_{GS} = 0\text{V}$

Typical switching energy losses as a function of drain current, 2nd device own body diode: $V_{GS} = 0\text{V}$



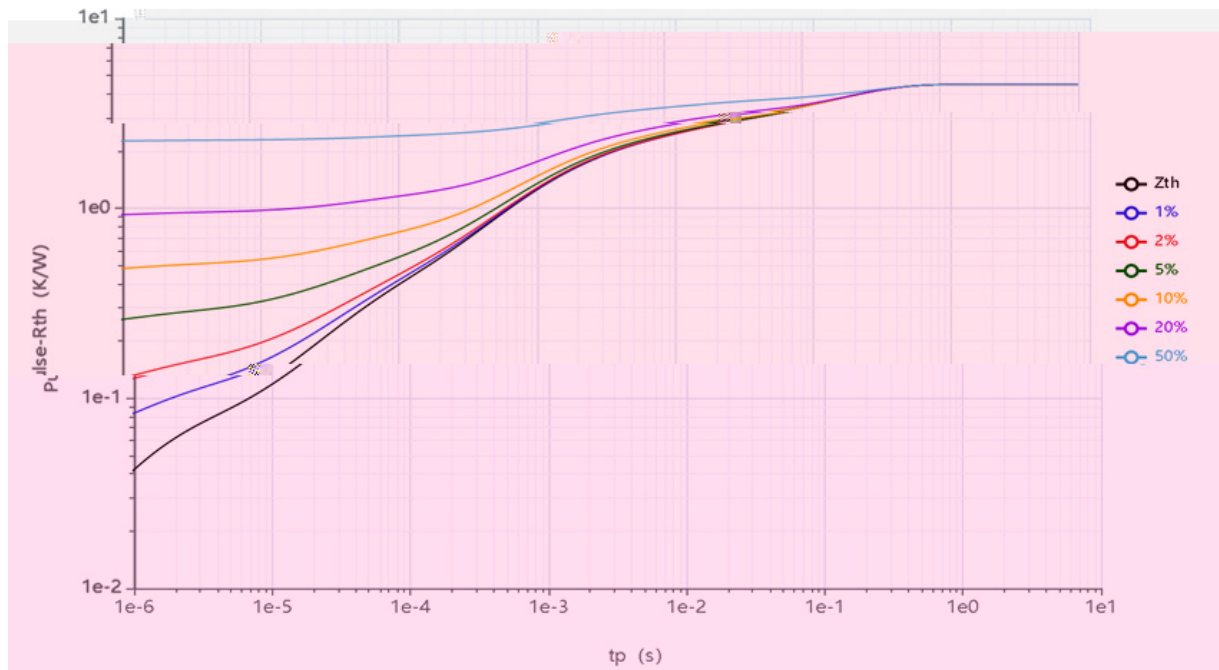
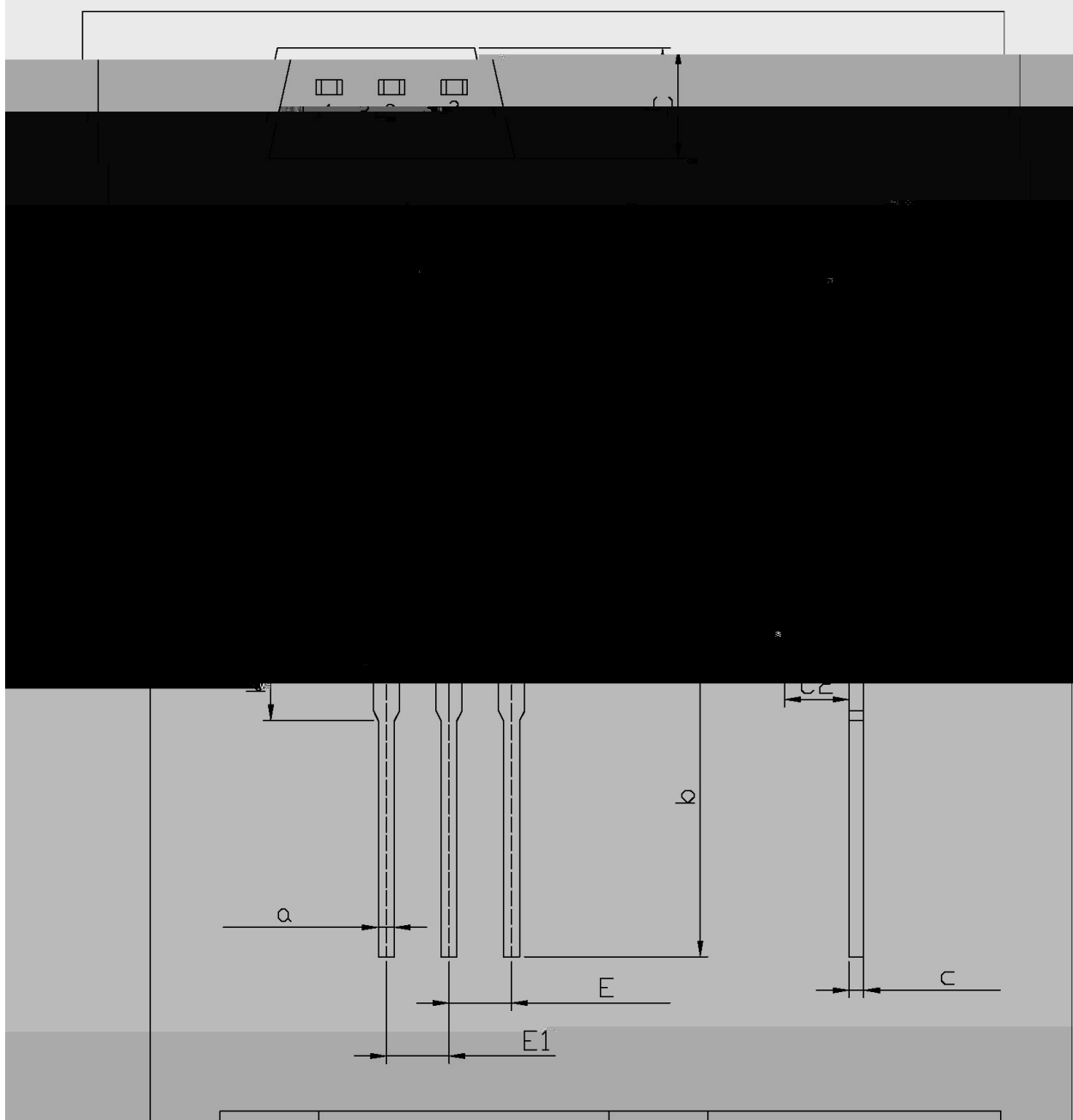


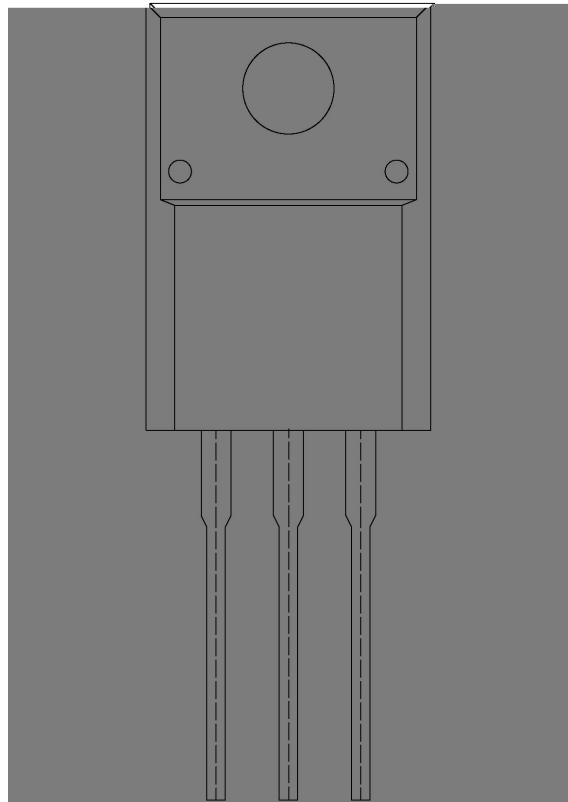
Fig24, Transient thermal resistance (MOSFET)

T0-220F

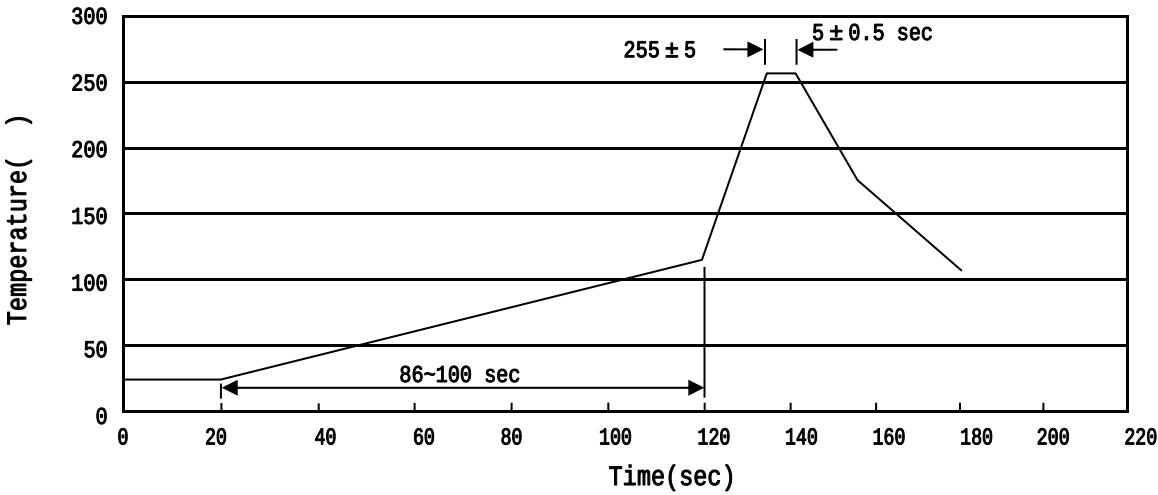
单位: mm



Dimensions In Millimeters			Dimensions In Millimeters		
Symbol	Min	Max	Symbol	Min	Max
C	4.3	4.7	b1	2.9	3.9
A	9.7	10.3	a	0.55	0.75
B	14.7	15.3	E	2.29	2.79
D	2.8	3.2	F	0.5	0.7



SC



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